Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D T_A = +25°C
30V	45mΩ @ V_{GS} = 10V	4.0 A
	50mΩ @ V_{GS} = 4.5V	3.5A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- DC-DC Converters
- Power management functions

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

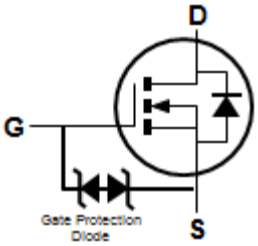
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)

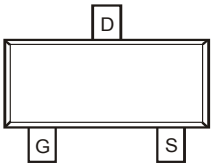
ESD PROTECTED

SOT23

Top View



Equivalent Circuit



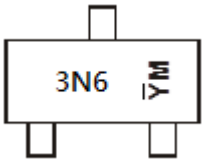
Top View

Ordering Information (Note 4)

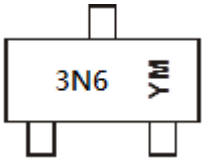
Part Number	Case	Packaging
DMN3053L-7	SOT23	3000/Tape & Reel
DMN3053L-13	SOT23	10000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Chengdu A/T Site



Shanghai A/T Site

3N6 = Product Type Marking Code
YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)
$\overline{Y}$M = Date Code Marking for CAT (Chengdu Assembly/ Test site)
Y or $\overline{Y}$ = Year (ex: A = 2013)
M = Month (ex: 9 = September)

Date Code Key

Year	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	U	V	W	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	4.0 3.5	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	35	A
Maximum Body Diode Forward Current (Note 6)			I_S	1.5	A

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	0.76	W
	T_A = +70°C		0.48	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	165	°C/W
	t<10s	$R_{\theta JA}$	114	°C/W
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.2	W
	T_A = +70°C		0.8	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	100	°C/W
	t<10s	$R_{\theta JA}$	69	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 30V, V_{GS} = 0V
Gate-Body Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±10V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	0.6	—	1.4	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	36 38 42 44	45 50 53 55	mΩ	V_{GS} = 10V, I_D = 4.0A V_{GS} = 4.5V, I_D =3.5A V_{GS} = 3.0V, I_D =3.0A V_{GS} = 2.5V, I_D =2.8A
Source-Drain Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 1.25A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	676	—	pF	V_{DS} = 15V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	54	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	42	—	pF	
Gate Resistance	R_g	—	15.5	—	Ω	V_{DS} = V_{GS} = 0V,f = 1.0MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	7.3	—	nC	V_{DS} = 15V, I_D = 4A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	17.2	—	nC	
Gate-Source Charge	Q_{gs}	—	1.2	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.9	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	2.0	—	ns	V_{DD} = 15V, V_{GS} = 10V, R_L = 15Ω, R_G = 6Ω
Turn-On Rise Time	t_r	—	5.5	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	152	—	ns	
Turn-Off Fall Time	t_f	—	32	—	ns	

Notes:
5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2 oz. Copper, single sided.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

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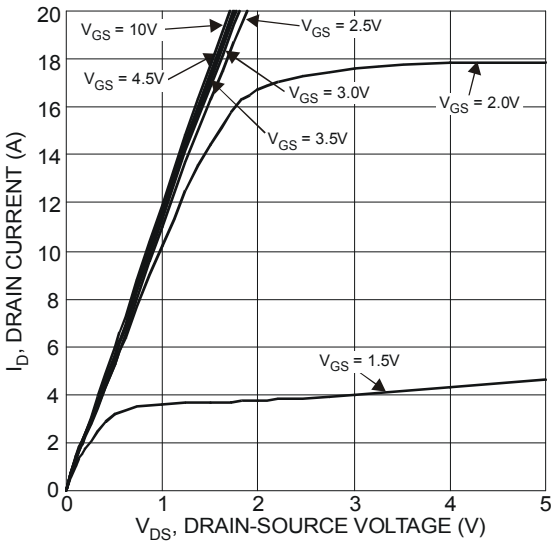

Figure 1 Typical Output Characteristics

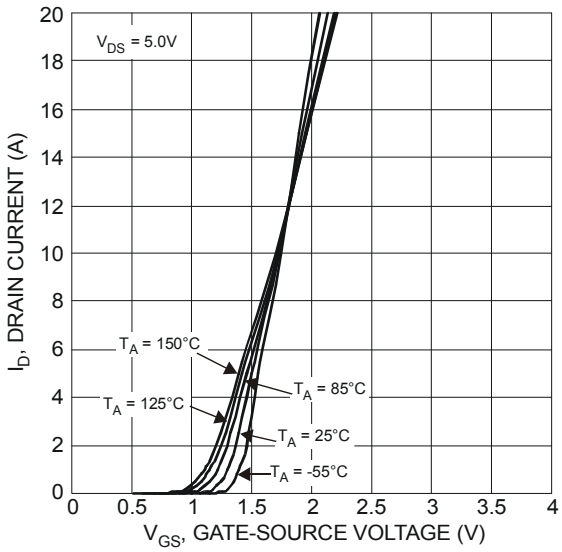

Figure 2 Typical Transfer Characteristics

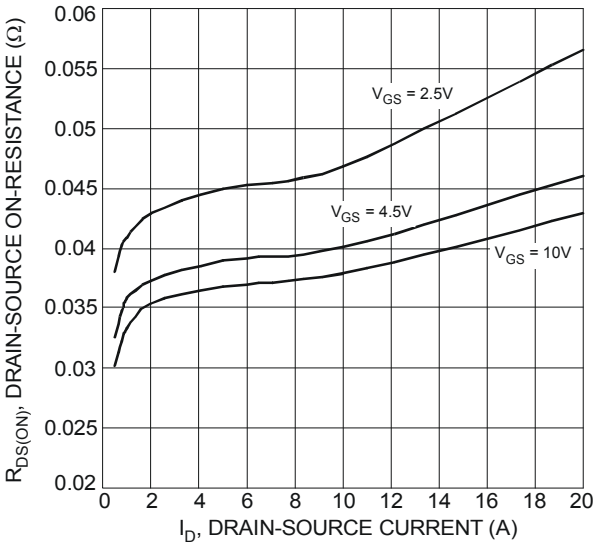

Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

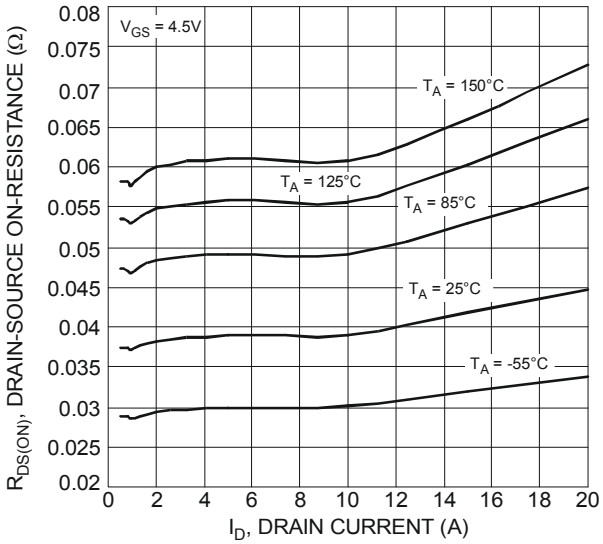

Figure 4 Typical On-Resistance vs. Drain Current and Temperature

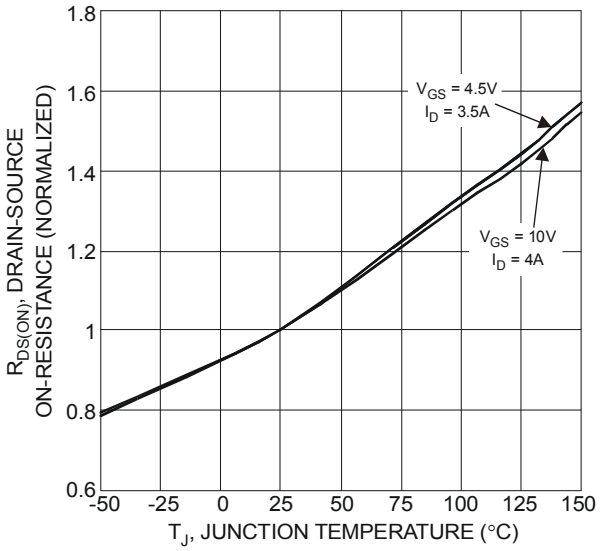

Figure 5 On-Resistance Variation with Temperature

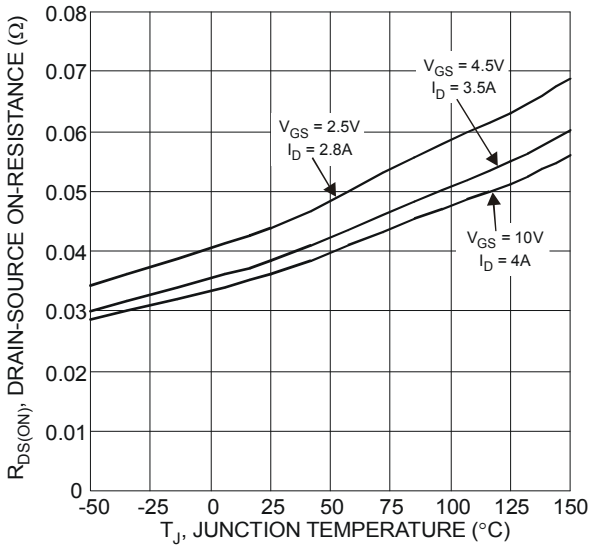

Figure 6 On-Resistance Variation with Temperature

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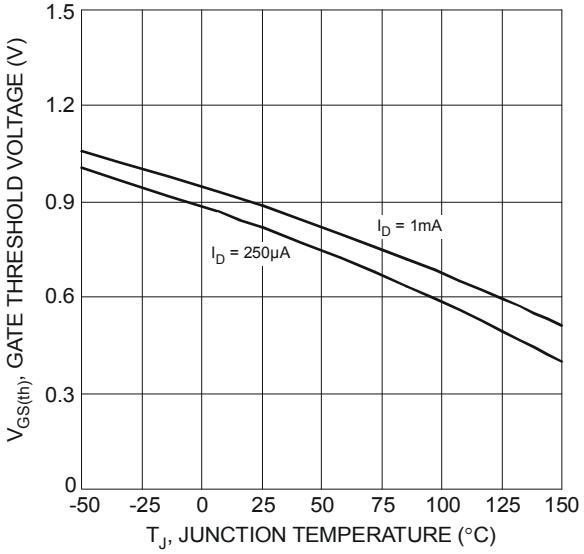

Figure 7 Gate Threshold Variation vs. Ambient Temperature

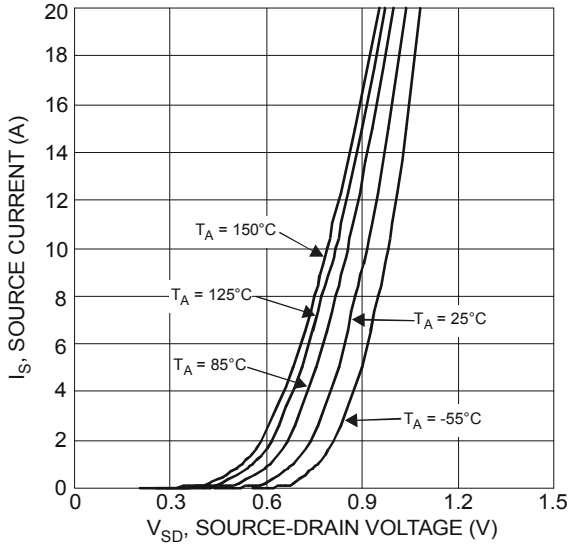

Figure 8 Diode Forward Voltage vs. Current

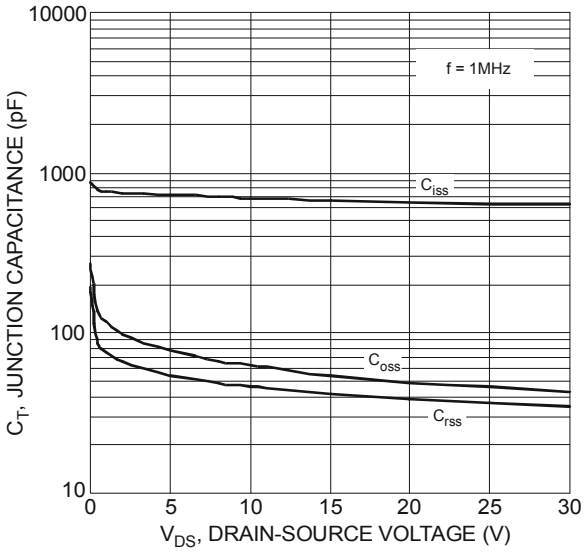

Figure 9 Typical Junction Capacitance

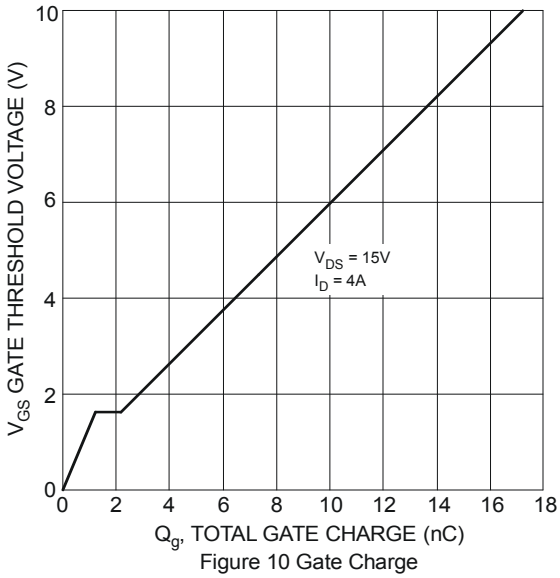

Figure 10 Gate Charge

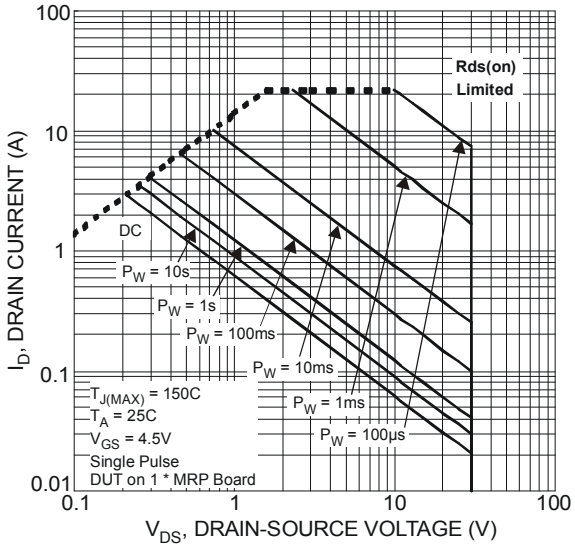

Figure 11 SOA, Safe Operation Area

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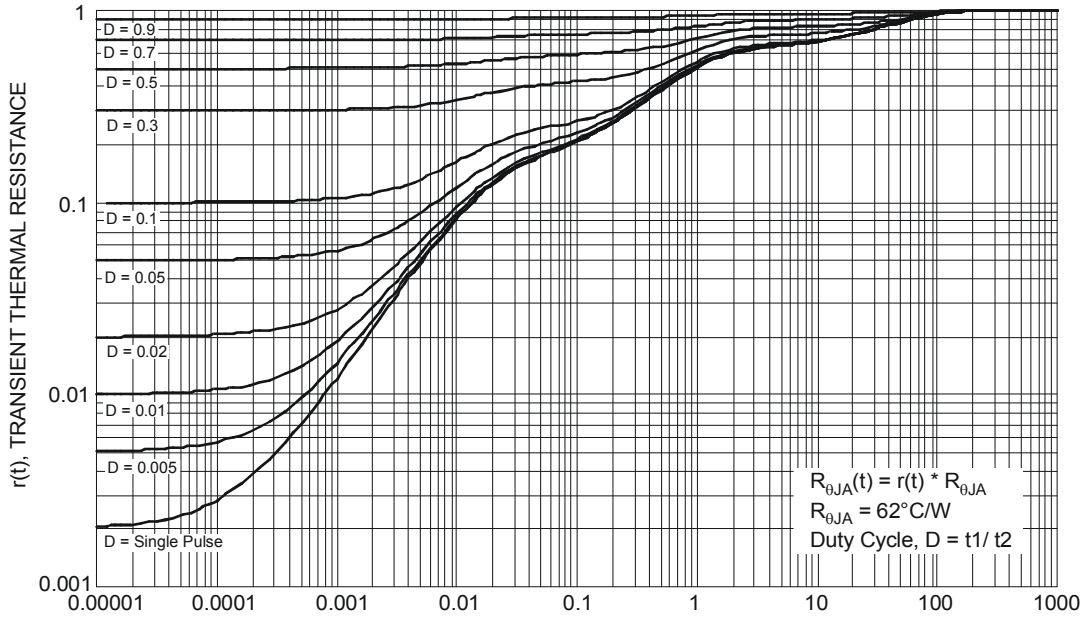
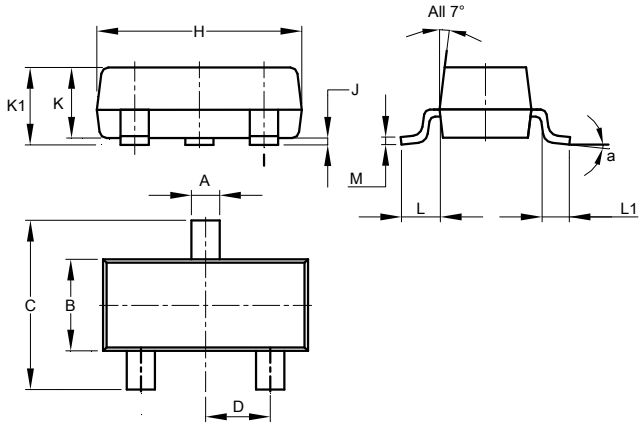


Figure 12 Transient Thermal Resistance

Package Outline Dimensions

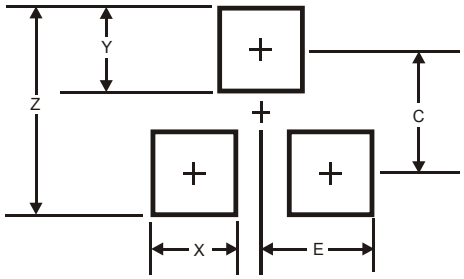
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	8°		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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